TVS Diode Arrays (SPA^M Family of Products) Lightning Surge Protection - SPLV2.8-4 Series

SPLV2.8-4 Series 2.8V 40A TVS Array



Pinout



Functional Block Diagram



NOT RECOMMENDED FOR NEW DESIGNS

SPLV2.8-4BTG is eventually going to be replaced by the SLVU2.8-4BTG TVS Diode Array with identical form, fit, and function. Please use this device for new or future designs and more detail can be found on Littelfuse.com

The SPLV2.8-4 was designed to protect low voltage, CMOS devices from ESD and lightning induced transients. There is a compensating diode in series with each low voltage TVS to present a low loading capacitance to the line being protected. These robust structures can safely absorb repetitive ESD strikes at ± 30 kV (contact discharge) per IEC61000-4-2 standard and each structure can safely dissipate up to 40A (IEC61000-4-5, t_p=8/20µs) with very low clamping voltages.

Features

- ESD, IEC61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC61000-4-4, 40A (5/50ns)
- Lightning, IEC61000-4-5, 40A (8/20µs)
- Low capacitance of 2pF per line
- Low leakage current of 1µA (MAX) at 2.8V

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• SOIC-8 pin (JEDEC MS-012) configuration allows for simple flow-through layout

Applications

- 10/100/1000 Ethernet
- Analog InputsBase Stations
- WAN/LAN Equipment
- Switching Systems
- Desktops, Servers, and Notebooks

Application Example



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TVS Diode Arrays (SPA" Fa

Lightning Surge Protection - SPLV2.8

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Electrical Characteristics (T_{op} = 25°C)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V _{RWM}	I _R ≤1μA			2.8	V
Reverse Breakdown Voltage	V _{BR}	I _T =2µA	3.0			V
Snap Back Voltage	V _{SB}	I _t =50mA	2.8			V
Reverse Leakage Current	ILEAK	V _R =2.8V (Each Line)			1	μA
Clamping Voltage ¹	V _c	I _{pp} =5A, t _p =8/20µs (Each Line)		7.0	8.5	V
Clamping Voltage ¹	V _c	I _{pp} =24A, t _p =8/20μs (Each Line)		13.9	15.0	V
		IEC61000-4-2 (Contact)	±30			kV
ESD Withstand Voltage ¹	V _{ESD}	IEC61000-4-2 (Air)	±30			kV
Dynamic Resistance	R _{DYN}	(V _{c2} - V _{c1}) / (I _{PP2} - I _{PP1}) (Each Line)		0.4		Ω
Diode Capacitance ¹	C _D	V _R =0V, f=1MHz (Each Line)		2.0	2.5	pF

Note: 1Parameter is guaranteed by design and/or device characterization.

Absolute Maximum Ratings					
Parameter	Rating	Units			
Peak Pulse Power (t _P =8/20µs)	600	W			
Peak Pulse Current (t _P =8/20µs)	40	А			
Operating Temperature	-40 to 85	°C			
Storage Temperature	-60 to 150	°C			

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Figure 1: Capacitance vs. Reverse Voltage



Figure 3: Pulse Waveform



Figure 2: Clamping Voltage vs. I



TVS Diode Arrays (SPA[™] Family of Products) Lightning Surge Protection - SPLV2.8-4 Series

Product Characteristics

Lead Plating	Matte Tin	
Lead Material	Copper Alloy	
Lead Coplanarity	0.0004 inches (0.102mm)	
Substitute Material	Silicon	
Body Material	Molded Epoxy	
Flammability	UL 94 V-0	

Notes

All dimensions are in millimeters
Dimensions include solder plating.

3. Dimensions are exclusive of mold flash & metal burr.

Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
Package surface matte finish VDI 11-13.

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Soldering Parameters

Reflow Condition		Pb – Free assembly	
Pre Heat	-Temperature Min (T _{s(min)})	150°C	
	-Temperature Max (T _{s(max)})	200°C	
	-Time (min to max) (t _s)	60 – 180 secs	
Average ra (T _L) to pea	amp up rate (Liquidus) Temp k	5°C/second max	
T _{S(max)} to T _L	- Ramp-up Rate	5°C/second max	
Reflow	- Temperature (T _L) (Liquidus)	217°C	
nellow	-Temperature (t _L)	60 – 150 seconds	
PeakTemp	erature (T _P)	260 ^{+0/-5} °C	
Time with Temperatu	in 5°C of actual peak ıre (t _p)	20 – 40 seconds	
Ramp-dov	vn Rate	5°C/second max	
Time 25°C	to peakTemperature (T _P)	8 minutes Max.	
Do not exceed		260°C	



Package Dimensions — Mechanical Drawings and Recommended Solder Pad Outline





Recommended Soldering Pad Outline (Reference Only)



Package	SOIC				
Pins	8				
JEDEC	MS-012				
	Millin	netres	Inches		
	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A1	0.10	0.25	0.004	0.010	
A2	1.25	1.65	0.050	0.065	
В	0.31	0.51	0.012	0.020	
C	0.17	0.25	0.007	0.010	
D	4.80	5.00	0.189	0.197	
E	5.80	6.20	0.228	0.244	
E1	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050) BSC	
L	0.40	1.27	0.016	0.050	

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SPLV2.8-4 Series

SPLV2.8-4

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TVS Diode Arrays (SPAT Family of Products)

Lightning Surge Protection

G= Green

Package B = SOIC-8

T= Tape & Reel

No. of channels

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art Marking System



No. of channels

Ordering Information

Part Number	Package	Marking	Min. Order Qty.
SPLV2.8-4BTG	SOIC-8	U2.8-4	2500

Embossed Carrier Tape & Reel Specification - SOIC Package

<u>SP LV2.8 -4 B T G</u>



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Part Numbering System

Silicon Protection Array (SPA™) Family of

TVS Diode Arrays

Series -

Currente e l	Millimetres		Inches			
Symbol	Min	Max	Min	Max		
E	1.65	1.85	0.065	0.073		
F	5.4	5.6	0.213	0.22		
P2	1.95	2.05	0.077	0.081		
D	1.5	1.6	0.059	0.063		
D1	1.50 Min		0.059 Min			
P0	3.9	4.1	0.154	0.161		
10P0	40.0 +/- 0.20		1.574 +,	1.574 +/- 0.008		
W	11.9	12.1	0.468	0.476		
Р	7.9	8.1	0.311	0.319		
A0	6.3	6.5	0.248	0.256		
B0	5.1	5.3	0.2	0.209		
К0	2	2.2	0.079	0.087		
t	0.30 +/- 0.05		0.012 +	/- 0.002		